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#### SUMMER- 19 EXAMINATION

Subject Name: Electronic Devices & Circuits Model Answer Subject Code:

17319

## Important Instructions to examiners:

- 1) The answers should be examined by key words and not as word-to-word as given in themodel answer scheme.
- 2) The model answer and the answer written by candidate may vary but the examiner may tryto assess the understanding level of the candidate.
- 3) The language errors such as grammatical, spelling errors should not be given more Importance (Not applicable for subject English and Communication Skills.
- 4) While assessing figures, examiner may give credit for principal components indicated in the figure. The figures drawn by candidate and model answer may vary. The examiner may give credit for any equivalent figure drawn.
- 5) Credits may be given step wise for numerical problems. In some cases, the assumed constant values may vary and there may be some difference in the candidate's answers and model answer.
- 6) In case of some questions credit may be given by judgement on part of examiner of relevant answer based on candidate's understanding.
- 7) For programming language papers, credit may be given to any other program based on equivalent concept.

| Q.  | Sub  | Answers   |            |  |  |
|-----|------|---|------------|--|--|
| No. | Q.   |   | Scheme     |  |  |
|     | N.   |   |            |  |  |
| 1   | Α    | Attempt any SIX:  | 12- Total  |  |  |
|     |      |   | Marks      |  |  |
|     | (a)  | Name two types of BJT & draw their symbols.   | 2M         |  |  |
|     | Ans: | Two types of BJT:   | 1M for     |  |  |
|     |      |   | types      |  |  |
|     |      | • PNP   |            |  |  |
|     |      |   |            |  |  |
|     |      | C C   |            |  |  |
|     |      |   | Symbols    |  |  |
|     |      | n-p-n transistor p-n-p transistor   |            |  |  |
|     |      |   |            |  |  |
|     |      |   |            |  |  |
|     | (b)  | Define Q-point  | 2M         |  |  |
|     | Ans: | Q-point:  | 2M for     |  |  |
|     |      | For proper operation of transistor in any application, we set fixed levels of certain   | correct    |  |  |
|     |      | voltages and currents in a transistor. These values of currents and voltages define the | definition |  |  |
|     |      | voltages and currents in a datasistor. These values of currents and voltages define the |            |  |  |

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|      | point, at which transistor operates. This point is called operating point. It is also known  |  |
|------|--|--|
|      | as quiescent point or Q point.   |  |
| (c)  | State the need and types of amplifier coupling.  | 2M   |
| Ans: | <ul> <li>Need of amplifier coupling:</li> <li>1. When ever large amplifier with very good impedance matching is required, a signal stage amplifier circuit will not able to amplify the signal to a large extent.</li> <li>2. Thus, a number of stages are required for amplification, for this output of the first stage is connected to the input of the second stage, this is called as cascade system or multistage system.</li> <li>3. The connection of output first stage to the input second stage is called coupling.</li> <li>4. In case of a multistage system, the very good coupling is very essential, or else there will be a large number of losses at the output.</li> <li>Types of amplifier coupling:</li> <li>1. R-C coupled amplifier</li> <li>2. Transformer coupled amplifier</li> <li>4. Inductance (LC) coupling</li> </ul> | 1M for<br>need<br>1M for<br>types                              |
| (d)  | Draw symbol for n-channel and p-channel MOSFET.  | 2M   |
| Ans: | Symbol n-channel and p-channel MOSFET:   | 1M for n<br>channel<br>symbol<br>1M for p<br>channel<br>symbol |
|      | (OR)   |  |

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|      | N-channel Enhancement -MOSFET P-channel Enhancement -MOSFET  |   |
|------|--|---|
| (e)  | State the necessity of tuned amplifier.  | 2M  |
| Ans: | Necessity of tuned amplifier:<br>1. Selection of the desired radio frequency signal.   | 1M for<br>each point                            |
|      | 2. Amplification of the selected signal to a selected voltage level.   |   |
| (f)  | List applications of power amplifier.  | 2M  |
| Ans: | Below are the applications of power amplifiers across different sectors:<br>1.Consumer Electronics: Audio power amplifiers are used in almost all consumer<br>electronic devices ranging from microwave ovens, headphone drivers, televisions,<br>mobile phones and Home theatre systems to theatrical and concert reinforcement<br>systems. | 1M each<br>for any 2<br>correct<br>applications |
|      | <b>2.Industrial:</b> Switching type power amplifiers are used for controlling most of the industrial actuator systems like servos and DC motors.   |   |
|      | <b>3.Wireless Communication:</b> High power amplifiers are important in transmission of cellular or FM broadcasting signals to users. Higher power levels made possible because of power amplifiers increases data transfer rates and usability. They are also used in satellite communication equipment.                                    |   |
| (g)  | Sketch p-channel JFET construction.  | 2M  |

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| Ans: | p- channel JFET constructional diagram:  | 2M for                      |  |  |  |
|------|--|-----------------------------|--|--|--|
|      | N-region P<br>Channel Channel G<br>G<br>S<br>S<br>S  | correct<br>diagram          |  |  |  |
| (h)  | State the working principle of UJT   | 2M                          |  |  |  |
| Ans: | Figure shows the equivalent circuit of a unijunction transistor with voltage source V <sub>EE</sub> connected across emitter and base 1 and V <sub>BB</sub> connected across base 1 and base 2. Hence the Emitter diode is reversed biased by a voltage drop across the r <sub>B1</sub> and its own barrier potential V <sub>D</sub> . Thus total reverse bias voltage across a diode is equal to sum of $\eta_V$ <sub>BB</sub> and V <sub>D</sub> . As long as the V <sub>EE</sub> is below the total reverse bias voltage across the diode, it remains reverse biased and there is no emitter current. However if the V <sub>EE</sub> voltage reaches or exceeds the value equal to $(\eta_v V_{BB} + V_D)$ , the diode conducts V <sub>EE</sub> , which causes the diode to conduct , is called peak point voltage. $V_{P} = \eta_v V_{BB} + V_D$ | 2M for<br>correct<br>answer |  |  |  |
|      | When the emitter current begins to flow ,the UJT is said to be fired, triggered or turned on.  |                             |  |  |  |
| В    | Attempt any TWO:   |                             |  |  |  |
| (a)  | Compare between CE, CB &CC configuration. (Any four points)  | 4M                          |  |  |  |
|      |  |                             |  |  |  |

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|      | 1.Input resistance                   | Moderate  | low   | Very high                         | comparison<br>points         |
|------|--------------------------------------|---|---|-----------------------------------|------------------------------|
|      | 2.output resistance                  | Moderate  | Very high   | low                               |                              |
|      | 3.voltage gain                       | highest   | high  | Equal to one                      |                              |
|      | 4.current gain                       | $\beta = \frac{IC}{IB}$   | $\alpha = \frac{IC}{IE}$  | $\mathbf{\gamma} = \frac{IE}{IB}$ |                              |
|      | 5.Applications                       | AF Applications   | HF<br>Applications  | Impedance<br>matching             |                              |
| (b)  | Draw the circuit diagram o obtained? | f based biased with e   | emitter feedback  | . How stability point i           | s 4M                         |
| Ans: | Circuit diagram of based             | biased with emitter   | feedback  |                                   | 2M for<br>circuit<br>diagram |
|      |                                      | (I <sub>c</sub><br>I <sub>b</sub> ↓<br>R <sub>b</sub> ↓I <sub>c</sub> C<br>B<br>V <sub>be</sub> E | $ \begin{array}{c} \mathbf{F}_{\mathbf{r}} + \mathbf{I}_{\mathbf{b}} + \mathbf{V}_{\mathbf{cc}} \\ \mathbf{K}_{\mathbf{c}} \\ \end{array} $ |                                   | 2M for<br>stability<br>point |
|      | Stability Point:                     |   |   |                                   |                              |

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| T    |  |            |
|------|--|------------|
|      | To find S:   |            |
|      | $S = \frac{(1+\beta)}{\beta}$  |            |
|      | $(1-\beta)\frac{\partial I_B}{\partial I_C}$   |            |
|      | ∂I <sub>R</sub>  |            |
|      | $\frac{1}{\partial I_C}$ is obtained by diff. $I_B$ WRT $I_S$  |            |
|      | $I_B = \frac{V_{CC} - I_C R_C - V_{BE}}{P_{CC} + P_{CC}}$  |            |
|      | $R_C + R_B$  |            |
|      | $\frac{\partial I_B}{\partial I_C} = \frac{-R_C}{R_C + R_B}$   |            |
|      | $S = \frac{(1+\beta)}{\beta}$  |            |
|      | $(1-\beta)\frac{-R_C}{R_C+R_B}$  |            |
|      | $ (1+\beta)$   |            |
|      | $(1+\beta)\frac{R_C}{R_C+R_B}$   |            |
|      | $S = \frac{(1+\beta)(R_c + R_B)}{2}$   |            |
|      | $R_{C} + R_{B} + \beta R_{C}$  |            |
|      | $S = \frac{(1+\beta)(R_C + R_B)}{R_C + (2\beta + 1)R_C}$   |            |
|      | $R_B + (\beta + 1)R_C$   |            |
| (c)  | State the need of regulation. Explain the concept of load & line regulation.   | 4M         |
| Ans: | Need of Regulation:  | 2M for     |
|      | The major disadvantage of a power supply is that the output voltage changes with the   | need of    |
|      | variations in the input voltage or the DC output voltage of the rectifier also increase  | regulation |
|      | similarly. In many electronic applications, it is desired that the output voltage, should remain constant regardless of the variations in the input voltage or load. In order to get |            |
|      | ensure this ;a voltage stabilizing device called voltage regulator is used.  |            |
|      | Load Regulation:   |            |
|      | The load regulation indicates the change in output voltage that will occur per unit  |            |
|      | change in load current.  |            |
|      | Mathematically   |            |
| 1    |  |            |
|      |  |            |

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| $Load Regulation = \frac{V_{NL} - V_{FL}}{\Delta I_L}$ The load regulation of voltage regulator is expressed in terms of $\mu v/\mu A$ .<br>Where, $V_{NL}$ is no load output voltage<br>$V_{FL}$ is full load voltage | 1M each<br>for load<br>and line<br>regulation |
|--|---|
| $\Delta I_L$ is change in laod current   |   |
| Line Regulation:   |   |
| The line regulation rating of a voltage regulator indicates the change in output voltage that will occur per unit change in the input voltage.   |   |
| $Line \ regulation = \frac{\Delta V_L}{\Delta V_S}$  |   |
| Where, $\Delta V_L$ is the change in output voltage in mV or $\mu V \Delta V_S$ is the change in input voltage in volts.   |   |

| Q.<br>No | Sub<br>Q.<br>N. | Answers   | Marking<br>Scheme         |
|----------|-----------------|---|---------------------------|
| 2        |                 | Attempt any FOUR:   | 16- Total<br>Marks        |
|          | (a)             | State the need of biasing and describe the concept of DC load line  | 4M                        |
|          | Ans<br>:        | <ul> <li>Need of Biasing for Transistor:</li> <li>The transistor should be biased in the active region if it is to be used for amplification and in saturation and cut off if it is used as a switch.</li> <li>2. The Q point should be adjusted approximately at the center of the load line for voltage amplifier application.</li> <li>3. The value of stability factor (S) should be as small as possible.</li> </ul> | 2M for need<br>of biasing |



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|          | (i) Stabilization   |                              |
|----------|---|------------------------------|
|          | (ii) Thermal runaway  |                              |
| Ans<br>: | Stabilization:<br>The process of making operating point independent of temperature changes or<br>variation in transistor parameter is known as stabilization.                                 | 2M for<br>stabilization      |
|          | The maintenance of the operating point stable is called the stabilization.  |                              |
|          | Thermal runaway:  |                              |
|          | Power<br>dissipation t ICEO t<br>Ict  | 2M for<br>Thermal<br>runaway |
|          | 1. The reverse saturation current in semiconductor devices changes with temperature.<br>The reverse saturation current approximately doubles for every 10 degree rise in<br>temperature.      |                              |
|          | 2.As the leakage current of transistor increases, collector current increases.  |                              |
|          | 3. The increase in power dissipation at collector base junction.  |                              |
|          | 4. This in turn increases the collector base junction causing the collector current current to further increase.  |                              |
|          | 5. This process becomes cumulative. and it is possible that the ratings of the transistor are exceeded. If it happens, the device gets burnt out. This process is known as "Thermal Runaway". |                              |
| (c)      | Draw the transfer characteristics for N-channel JFET.   | 4M                           |
| Ans<br>: | Transfer characteristics for N-channel JFET:  | 2M for<br>characteristi<br>c |
|          | V <sub>GS (off)</sub><br>= V <sub>p</sub><br>- Gate-to-source0  | 2M for label                 |

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| (a)             | Draw th  | ne circuit of using transistor as a s  | witch & explain its workir   | ng.   | 4M  |
|-----------------|--|--|--|---|---|
| Ans<br>:        |  |  | Ro   |   | 2M for<br>diagram   |
|                 | a) Whe<br>switch.  | vcc  | it works in saturation reg   | gion & act as closed  | 2M for<br>explanatior   |
|                 | b) Whe<br>switch.  | n both junctions are reverse biase   | ed it works in cutoff regio  | n & act as open   |   |
|                 | c) If inp<br>switch.   | ut is not given to base ,transistor  |  | e off. IC=0,Acts as open  |   |
| (e)             | c) If inp<br>switch.<br>d) when<br>starts f  | ut is not given to base ,transistor<br>n input is applied to base above 0.<br>owing ,Transistor acts as close sw   | 7V ,transistor becomes (<br>itch.  | DN, Diode is ON. Ic   | 4M  |
| (e)<br>Ans<br>: | c) If inp<br>switch.<br>d) when<br>starts f<br>Compa<br>Sr<br>No.  | n input is applied to base ,transistor<br>owing ,Transistor acts as close sw<br>re between positive and negative<br><b>Parameter</b>   | 7V ,transistor becomes (<br>itch.<br>feedback. (four points)<br><b>Positive Feedback</b>   | Negative Feedback   | 4M<br>1M each fo<br>any four                                    |
| (e)<br>Ans<br>: | c) If inp<br>switch.<br>d) when<br>starts f<br>Compa<br>Sr<br>No.<br>1                                   | n input is applied to base shove 0.<br>owing ,Transistor acts as close sw<br>re between positive and negative<br><b>Parameter</b><br>Overall Phase shift   | 7V ,transistor becomes (<br>itch.<br>feedback. (four points)<br><b>Positive Feedback</b><br>0 degree or 360<br>degree  | Negative Feedback   | 4M<br>1M each fo<br>any four<br>correct<br>comparison<br>points |
| (e)<br>Ans<br>: | c) If inp<br>switch.<br>d) when<br>starts f<br>Compa<br>Sr<br>No.<br>1<br>2                              | n input is applied to base above 0.<br>owing ,Transistor acts as close sw<br>re between positive and negative<br><b>Parameter</b><br>Overall Phase shift<br>Input voltage  | 7V ,transistor becomes (<br>itch.<br>feedback. (four points)<br><b>Positive Feedback</b><br>0 degree or 360<br>degree<br>Increases   | Negative Feedback         180 degree         Decreases  | 4M<br>1M each fo<br>any four<br>correct<br>compariso<br>points  |
| (e)<br>Ans<br>: | c) If inp<br>switch.<br>d) when<br>starts f<br>Compare<br>Sr<br>No.<br>1<br>2<br>3                       | n input is applied to base above 0.<br>owing ,Transistor acts as close sw<br>re between positive and negative<br>Parameter<br>Overall Phase shift<br>Input voltage<br>Output voltage   | 7V ,transistor becomes (<br>itch.<br>feedback. (four points)<br><b>Positive Feedback</b><br>0 degree or 360<br>degree<br>Increases   | N, Diode is ON. Ic         Negative Feedback         180 degree         Decreases         Decreases   | 4M<br>1M each fo<br>any four<br>correct<br>comparison<br>points |
| (e)<br>Ans<br>: | c) If inp<br>switch.<br>d) when<br>starts f<br>Compare<br>Sr<br>No.<br>1<br>2<br>3<br>4                  | n input is applied to base above 0.<br>owing ,Transistor acts as close sw<br>re between positive and negative<br>Parameter<br>Overall Phase shift<br>Input voltage<br>Output voltage<br>Feedback signal & Input signal   | 7V ,transistor becomes (<br>itch.<br>feedback. (four points)<br>Positive Feedback<br>0 degree or 360<br>degree<br>Increases<br>Increases<br>Are in phase   | Negative Feedback         180 degree         Decreases         Decreases         Are out of phase   | 4M<br>1M each fo<br>any four<br>correct<br>compariso<br>points  |
| (e)<br>Ans<br>: | c) If inp<br>switch.<br>d) when<br>starts fi<br>Compai<br>Sr<br>No.<br>1<br>2<br>3<br>4<br>5             | ut is not given to base ,transistor<br>n input is applied to base above 0.<br>owing ,Transistor acts as close sw<br>re between positive and negative<br>Parameter<br>Overall Phase shift<br>Input voltage<br>Output voltage<br>Feedback signal & Input signal<br>Voltage Gain          | 7V ,transistor becomes (<br>itch.<br>feedback. (four points)<br>Positive Feedback<br>0 degree or 360<br>degree<br>Increases<br>Are in phase<br>Increases   | Negative Feedback         180 degree         Decreases         Are out of phase         Decreases   | 4M<br>1M each fo<br>any four<br>correct<br>comparison<br>points |
| (e)<br>Ans<br>: | c) If inp<br>switch.<br>d) when<br>starts f<br>Compa<br>Compa<br>Sr<br>No.<br>1<br>2<br>3<br>4<br>5<br>6 | ut is not given to base ,transistor<br>n input is applied to base above 0.<br>owing ,Transistor acts as close sw<br>re between positive and negative<br>Parameter<br>Overall Phase shift<br>Input voltage<br>Output voltage<br>Feedback signal & Input signal<br>Voltage Gain<br>Noise | 7V ,transistor becomes (         itch.         feedback. (four points)         Positive Feedback         0 degree or 360         degree         Increases         Are in phase         Increases         Increases         Increases         Increases         Increases         Increases         Increases | Negative Feedback         180 degree         Decreases         Are out of phase         Decreases         Decreases         Decreases         Decreases         Decreases         Decreases         Decreases         Decreases         Decreases         Decreases | 4M<br>1M each fo<br>any four<br>correct<br>comparison<br>points |

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|          | 8                  | Applications                     |  | Oscillators, Schmitt<br>triggers                       | Amplifier           |                                    |
|----------|--------------------|----------------------------------|--|--|---------------------|------------------------------------|
| (f)      | List the           | ICs used for po                  | sitive and negative                    | e voltage regulation with                              | two example each.   | 4M                                 |
| Ans<br>: | IC 78xx<br>IC 79xx | (7805,7806, 78<br>(7905, 7906,79 | 08,,7812,7815,781<br>08,7912, 7915, 79 | .8)-Positive Voltage Regu<br>18) - Negative Voltage Re | ilator.<br>egulator | 2M for<br>correct IC<br>Number and |
|          | Exampl<br>7805=    | e:<br>+5v                        | 7905= -5v                              |  |                     | 2M for<br>example                  |
|          | 7806=              | +6v                              | 7906= -6v                              |  |                     | (Two<br>examples                   |
|          | 7808=              | +8v                              | 7908= -8v                              |  |                     | positive and                       |
|          | 7812=              | +12v<br>+15v                     | /912= -12v<br>7915= -15v               |  |                     | voltage<br>regulator)              |
|          | 7818=              | +18v                             | 7918= -18v                             |  |                     |                                    |

| Q.<br>No. | Sub<br>Q.<br>N. | Answers  | Marking<br>Scheme  |
|-----------|-----------------|--|--------------------|
| 3         |                 | Attempt any FOUR:  | 16- Total<br>Marks |
|           | (a)             | In CE configuration if $\beta$ = 90, leakage current I <sub>CEO</sub> = 40µA, base current is 0.4mA, determine I <sub>c</sub> and I <sub>E</sub> | 4M                 |
|           | Ans:            | Given:   |                    |
|           |                 | β = 90   |                    |
|           |                 | I <sub>CEO</sub> = 40μA  | Each               |
|           |                 | I <sub>B</sub> = 0.4mA   | 2M                 |
|           |                 | Required :   |                    |

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|      | $l_{c} = ?$ Solut $l_{c} = \beta$ $= 90$ $l_{c} = 3$ $l_{E} = l_{c}$ $l_{E} = 3$ | and $I_E = ?$<br>tion:<br>$I_B + I_{CEO}$<br>$D \times 0.4 \times 10^{-3} + 40 \times 10^{-6}$<br>6.04 mA<br>$+ I_B = 36.04$ mA $+ 0.4$ mA<br>6.44 mA |  | Each ans :<br>2M       |
|------|--|---|--|------------------------|
| (b)  | Com  | pare FET and BJT. (four points)   |  | 4M                     |
| Ans: | Sr.<br>no  | FET   | BJT  | Any four<br>points: 4M |
|      | 1.   | It is unipolar device i.e. current in the device is carried either by electrons or holes  | It is bipolar device i.e. current in the device is carried either by both electrons & holes  |                        |
|      | 2.   | It is a voltage controlled device i.e.<br>voltage at the gate (or drain) terminal<br>controls amount of current flowing<br>through the device.        | It is a current controlled device i.e. the<br>base current controls the amount of<br>collector current.                                |                        |
|      | 3.   | It has a negative temperature co-<br>efficient at high current levels. It<br>means that current decreases as<br>temperature increases.                | It has a positive temperature co-<br>efficient at high current levels. It<br>means that current increases as<br>temperature increases. |                        |
|      | 4.   | It has relatively lower gain bandwidth product as compared to BJT.  | It has relatively higher gain bandwidth product as compared to FET.  |                        |
|      | 5.<br>6.   | It is less noisy.<br>It is relatively immune to radiation.  | It is comparatively more noisy.<br>It is susceptible to radiation  |                        |
|      | -  |   | · · · ·  | 1                      |



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| Ans: | $ \begin{array}{c} \bigvee_{v} \bigvee_{v} & \bigvee_{$ | Circuit<br>diagram :<br>1M<br>Working:<br>2M<br>Waveform :<br>1m |
|------|---|--|
| (d)  | Draw the frequency response of DC amplifier. Comment on it.   | 4M   |
| Ans: | Trequency response:   | Response :<br>2M   |

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17319 Subject Name: Electronic Devices & Circuits Subject Code: Model Answer A step down transformer will step down the voltage from the ac mains to the required voltage level. The turn's ratio of the transformer is so adjusted such as to obtain the required voltage value. The output of the transformer is given as an input to the rectifier circuit. **Rectifier:-**Rectifier is an electronic circuit consisting of diodes which carries out the rectification process. The input to a rectifier is ac whereas its output is unidirectional pulsating dc. Usually a full wave rectifier or a bridge rectifier is used to rectify both the half cycles of the ac supply (full wave rectification). Filter :-The rectified voltage from the rectifier is a pulsating dc voltage having very high ripple content. Hence a filter is used. **Regulator:** This is the last block in a regulated DC power supply. The output voltage or current will change or fluctuate when there is change in the input from ac mains or due to change in load current at the output of the regulated power supply or due to other factors like temperature changes. This problem can be eliminated by using a regulator. A regulator will maintain the output constant even when changes at the input or any other changes occur. (f) Draw the circuit of Zener diode as a voltage regulator and explain its working. 4M Circuit Ans: diagram : 2M ٧R Unregulated Voltage zener diode Working

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For proper operation, the input voltage Vi must be greater than the Zener • voltage Vz. This ensures that the Zener diode operates in the reverse breakdown Working : condition. The unregulated input voltage Vi is applied to the Zener diode. 2M From fig, output voltage is equal to zener voltage and load voltage. Suppose this input voltage exceeds the Zener voltage. This voltage operates the Zener diode in reverse breakdown region and maintains a constant voltage, i.e. Vz = Vo ----- (1) The input current is given by,  $I_s = (Vi - Vz) / Rs$  ------ (2) We know that the input current  $I_S$  the sum of Zener current Iz and load current IL. Therefore,  $I_{S} = I_{Z} + I_{L}$  ------ (3) or |z = |s - h|As input voltage Vi increases, then input current Is increases from equation no. (2), then Iz current increases from equation no. (3), hence zener voltage remains Vz constant (according to reverse bias of zener diode characteristics). • Since zener voltage is equal to output voltage from equation no. (1). Therefore output voltage Vo remains constant. Thus, a Zener diode acts as a voltage regulator and the fixed voltage is maintained across the load resistor RL.

| Q.<br>No. | Sub Q.<br>N. | Answers  | Marking<br>Scheme     |
|-----------|--------------|--|-----------------------|
| 4         |              | Attempt any FOUR:  | 12- Total<br>Marks    |
|           | (a)          | Draw the drain characteristics of p-channel FET and explain. | 4M                    |
|           | Ans:         | Drain characteristics:-                                      | Characeristics-<br>2M |

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17319 Subject Code: Subject Name: Electronic Devices & Circuits Model Answer The gate to source voltage is set to zero volts by the direct connection from one terminal to the other & voltage  $V_{DS}$  is applied across the drain to source terminals. This Working result the flow of current is positively charged holes. Principle-2M When gate is negative with respect to source then the electrons present under the oxide layer are pushed downward into the substrate with a repulsive force and draws additional holes from the N type substrate. Thus drain current (I<sub>D</sub>) increases as increase in negative value. For positive voltage at gate, the gate will tend to repel holes towards N type substrate and attract electrons from the substrate toward insulated layer. Recombination occurs between electron & holes that will reduce the number of free carriers in the channel for conduction. So drain current reduces. The value of voltage of VGS at which drain current nearly becomes zero is called cut off voltage. (d) Draw the circuit diagram of complementary symmetry Class B push-pull amplifier and 4M describe its working. Diagram of complementary symmetry Class B push-pull amplifier: Ans: Diagram-2M Vcc Positive R<sub>1</sub> NPN half-cycle C<sub>1</sub> Input R<sub>B1</sub> Signal Rι Resistor Biasing  $R_{B2}$ TR<sub>2</sub>  $C_2$ Negative half-cycle  $R_2$ PNP Working: Working-2M The above circuit employs a NPN transistor and a PNP transistor connected in push pull configuration. When the input signal is applied, during the positive half cycle of the input signal, the NPN transistor conducts and the PNP transistor cuts off. During the negative half cycle, the NPN transistor cuts off and the PNP transistor conducts.

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|       | In this w | av. the NPN transi         | stor amplifies during    | positive half cycle of t | the input, while |          |
|-------|-----------|----------------------------|--------------------------|--------------------------|------------------|----------|
|       |           | cictor amplifica du        | ring nogative half are   | lo of the input Ac the   | transistors are  |          |
|       |           | isistor amplifies du       |                          | the of the input. As the | transistors are  |          |
|       | both con  | nplement to each o         | other, act symmetrical   | ly while being connect   | ed in push pull  |          |
|       | configura | ation of class B, th       | is circuit is termed as  | s Complementary sym      | metry push pull  |          |
|       | class B a | amplifier.                 |                          |                          |                  |          |
| (e)   | Compare   | between class A a          | ind class B amplifier or | the basis of             |                  | 4M       |
| (0)   | (i)       |                            |                          |                          |                  |          |
|       | (i)       | Efficiency                 |                          |                          |                  |          |
|       | (11)      | Power<br>Position of O- no | vint                     |                          |                  |          |
|       | (iv)      | O/P distortion             |                          |                          |                  |          |
| Ans:  |           |                            |                          |                          |                  | 4M(1N    |
|       |           |                            |                          |                          |                  | for each |
|       |           | Parameter                  | Class A                  | Class B                  | ]                | point)   |
|       |           | Efficiency                 | lowest efficiency        | Above 78.5%              | -                |          |
|       |           |                            | 25% to 50%               |                          |                  |          |
|       |           |                            |                          |                          |                  |          |
|       |           | Power                      | less                     |                          |                  |          |
|       |           |                            |                          | More than class A        |                  |          |
|       |           | Position of Q              | Q point is at the        |                          | -                |          |
|       |           | point                      | centre of load           | On X axis                |                  |          |
|       |           |                            | line.                    |                          |                  |          |
|       |           | O/D disartian              |                          |                          | _                |          |
|       |           |                            | NO distortion            | Iviore than class A      |                  |          |
| (f)   | Draw the  | circuit diagram of         | Bootstrap's time base    | e generator and explain  | n its working.   | 4M       |
| Anci  |           | iagram                     |                          |                          |                  | Diagram  |
| AIIS: |           | lagidiii                   |                          |                          |                  |          |
|       | 1         |                            |                          |                          |                  | 1        |

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that the output voltage is coupled through the capacitor  $(C_1)$  to the diode.

Since the value of capacitor  $(C_1)$  is much larger than that of capacitor (C), the voltage across capacitor  $(C_1)$  practically remains constant.

Thus voltage drop across resistor (R) and hence current  $(I_R)$  remains constant, means capacitor C is charged with constant current.



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|  | This causes voltage across capacitor C (and hence the output voltage) to increase linearly with time |  |
|--|--|--|
|  | The circuit pulls itself up by its own bootstrap and hence it is known as bootstrap                  |  |
|  | sweep circuit.   |  |

Model Answer

| Q.<br>No. | Sub<br>Q.<br>N. | Answers   | Marking<br>Scheme                |
|-----------|-----------------|---|----------------------------------|
| 5         |                 | Attempt any FOUR:   | 16- Total<br>Marks               |
|           | (a)             | Draw the input and output characteristics of CE configuration.  | 4M                               |
|           | Ans:            | Input characteristics of CE configuration:<br>$I_{B} = V_{CE1} = V_{CE2} = V_{CE1}$ $V_{CE2} > V_{CE1} = V_{CE2} = V_{CE1}$ | input<br>characteristics-<br>2M  |
|           |                 | Output characteristics of CE configuration:   | output<br>characteristics-<br>2M |

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Ans: Note: Any other configuration explanation also can be considered. Diagram-1.5M R. С, Working principle-1.5M **Operation of FET amplifier:** When small a.c. signal is applied to the gate, it produces variation in the gate to source voltage. This results in variation in the drain current. As the gate to source voltage increases, the drain current also increases. As the result of this, the voltage drop across resistor (RD) also increases. This causes the drain voltage to decrease. It means positive half cycle of the input voltage produces the negative half cycle of the output voltage. (ie.) the output voltage is 180° out of phase with the input voltage. Application-Application: 1M(Any two) Buffer amplifier Low noise amplifier Cascade amplifier Chopper amplifier State the basic principle of piezoelectric crystal and draw the circuit diagram of crystal 4M (e) oscillator. **Basic Principle:** Ans: Basic principle-2M



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| Note: Other method for regulator also can be consider. |  |
|--|--|
|  |  |
|  |  |
|  |  |
|  |  |

| Q.<br>No. | Sub Q. N. | Answers   | Marking<br>Scheme                     |
|-----------|-----------|---|---------------------------------------|
| 6         |           | Attempt any FOUR:   | 16- Total Ma                          |
|           | (a)       | Draw the circuit of voltage divider for BJT & explain its working.  | 4M                                    |
|           | Ans:      | $(I+I_0) \downarrow I_0 I_0 I_0 I_0 I_0 I_0 I_0 I_0 I_0 I_0$ | Circuit diagra<br>: 2M<br>Working: 2M |

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|    |      | $V_{TH} = (R_2 - R_1 + R_2) \cdot V_{CC}$ And the equivalent resistance.<br>$R_{TH} = R_1 ll R_2 = (R_1 - R_2) - (R_1 + R_2)$ Applying KVL to the base emitter loop of this circuit,<br>$V_{TH} = I_B R_{TH} + V_{BE} + I_E R_E$ $I_B = (V_{TH} - V_{BE}) (I_E = (\beta + 1) I_B) - (R_{TH} + (\beta + 1) R_E)$ $I_B = (V_{TH} - (V_{TH} >> V_{BE}, (\beta + 1) = \beta) - (R_{TH} + \beta_{RE})$ $I_C = \beta I_B$ $I_C = V_{TH} - (R_E >> R_{TH} / \beta)$ $I_C = V_{TH} / R_E - (R_E >> R_{TH} / \beta)$ Applying KVL to the output section, we get $V_{CC} = I_C R_C + V_{CE} + I_E R_E$ |                     |
|----|------|--|---------------------|
| () | b)   | $v_{CE} - v_{CC} - i_C (K_C + K_E)$  | 454                 |
| () | 0)   | Draw the transistorized series voltage regulator circuit and explain its working.  | 4101                |
| A  | Ans: | Unregulated voltage  | Diagram : 2M        |
|    |      | <ul> <li>Explanation :</li> <li>In this circuit transistor acts as a control element. This transistor is connected in series with the load hence the circuit is called as Series Voltage Regulator. Other components in the circuit are Zener diode (Vz), and resistor R.</li> </ul>   | Explanation :<br>2M |

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|-----------|---|---|--|--|-------------------------------------|
|           | <ul> <li>Zener diode V<sub>Z</sub> is operat<br/>V<sub>Z</sub>.</li> <li>As V<sub>Z</sub> &amp; V<sub>BE</sub> of the transi<br/>constant. To find output</li> </ul>  | ed in breakdown reg<br>stor are constant, ou<br>voltage Vo.   | ion and provides cor<br>tput voltage across  | nstant voltage<br>R <sub>L</sub> will also be                              |                                     |
|           | Applying KVL to o/p loop $V_{BE} + I_LR_L - V_Z =$<br>Therefore, $V_O = I_LR_L = V_Z$<br>$V_O = V_Z - V_{BE}$<br>If output voltage increa<br>decreases and I <sub>C</sub> decreas<br>across the transistor and<br>$V_O=Vin - V_{CE}$<br>If the output voltage decr<br>the output voltage is reg | of the circuit<br>0<br>$-V_{BE}$<br>ses then $V_{BE}$ decrea<br>ses. This will increas<br>$V_0$ will be regulated<br>reases, then exactly of<br>ulated. | ases. Due to reduct<br>se the collector to en<br>this is because<br>opposite action will t | ion in V <sub>BE</sub> , I <sub>B</sub><br>mitter voltage<br>ake place and |                                     |
| (c)       | State and explain Barkhausen's o  | criteria of oscillators   |  |  | 4M                                  |
| Ans:      | <ul> <li>Statement of Barkhause</li> <li>To produce sustained ose</li> <li>Av β ≥ 1</li> <li>Phase shift between the</li> </ul>   | en's criteria:<br>cillations, an oscillat<br>input and output sig   | or circuit must satist<br>nals must be equal t   | fy<br>to 360° or 0°  | Statement                           |
|           | $V_{i} \downarrow \downarrow$  | <ul> <li>Heredback Vo</li> <li>Feedback Vo</li> <li>Heredback β</li> <li>Heredback β</li> </ul>   | vot  |  |                                     |
|           | <ul> <li>In oscillator positive feed<br/>Voltage gain of feedback</li> </ul>  | lback is used.<br>k amplifier is,   |  |  | Explanatio<br>(diagram<br>optional) |

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|      | $Avf = \frac{Av}{1 - Av\beta}$ Where, Av = open loop gain<br>$\beta$ = feedback factor<br>If Av $\beta$ = 1<br>Then 1- Av $\beta$ = 0<br>And will increase to infinity but in actual practice output of feedback amplifier<br>cannot be infinite, therefore 1-Av $\beta$ =0 represents, output voltage whose<br>frequency is completely different from the input signal.<br>• The amplifier reverses the phase of an input signal at its output (means it gives<br>180° phase shift) in order to provide positive feedback, the feedback network<br>must provide a phase shift of 180°. So that total phase shift of 360° or 0° at the<br>amplifier input.<br>• The above two condition for positive feedback i.e. Av $\beta$ =1 and net phase shift<br>around loop equal to 360° or 0° are called Barkhausen Criterion of Oscillation.  |                             |
|------|--|-----------------------------|
| (d)  | Draw the circuit of single tuned amplifier and state its operating principle.  | 4M                          |
| Ans: | Va C<br>Va C | Any Circuit<br>diagram : 2M |
|      | Operating Principle:   | Operating<br>Principle : 2N |

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|      |  | 1                                     |
|------|--|---------------------------------------|
|      | The working of tuned voltage amplifier may be understood by considering a radio frequency signal, to be amplified applied at the input of the amplifier. The resonant frequency of the tuned circuit is made equal to the frequency of the input signal by changing the value of capacitor (C) and inductor (L). When the frequency of the tuned circuit becomes equal to that of the input signal a large signal appears across the output terminals. |                                       |
|      | If the input signal is a complex wave (i.e. it contains many frequency components.) in<br>that case the frequency with input frequency equal to the resonant frequency will be<br>amplified. And all the other frequencies will be rejected by the tuned circuit.  |                                       |
| (e)  | Draw the labeled circuit of RC phase shift oscillator. State the formula for frequency of oscillator.  | 4M                                    |
| Ans: | Frequency of oscillation is given by,<br>$f = \frac{1}{2\pi(\sqrt{6})CR}$  | Circuit diagra<br>: 3M<br>Formula :1M |
| (f)  | Draw the characteristics of UJT and state its working principle.   | 4M                                    |









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